AMENDMENTS TO THE CLAIMS

Claims 1-21. (Cancelled)

22. (Previously Presented) A semiconductor device comprising:

a semiconductor chip;

at least a first electrode formed on a first major surface of said semiconductor chip;

at least a second electrode formed on a second major surface of said semiconductor chip opposite to said first major surface;

at least a conductive member connecting said first electrode to said second electrode and covering a side surface of said semiconductor chip; and

a conductive line pattern formed on said second major surface and extending from said second electrode, wherein said conductive line pattern is separate from said conductive member.

23. (Previously Presented) A composite semiconductor device structure, comprising at least two semiconductor devices, wherein

each of said semiconductor devices include:

a semiconductor chip;

at least a first electrode formed on a first major surface of said semiconductor chip;

at least a second electrode formed on a second major surface of said semiconductor chip opposite to said first major surface;

at least a conductive member connecting said first electrode to said second electrode and covering a side surface of said semiconductor chip;

said at least two semiconductor devices are stacked on each other, and

a conductive member of a lower one of said semiconductor devices is directly connected to a conductive member of an upper one of said semiconductor devices.

24. (Currently Amended) A composite semiconductor device structure, comprising ~~at least~~ two semiconductor devices, wherein

each of said semiconductor devices include:

a semiconductor chip;

~~at least~~ a first electrode formed on a first major surface of said semiconductor chip;

an insulating layer formed on a second major surface of said semiconductor chip opposite to said first major surface;

~~at least~~ a conductive member connected to said first electrode and covering and fixing to a side surface of said semiconductor chip;

said ~~at least~~ two semiconductor devices are stacked on each other, and

a conductive member of a lower one of said semiconductor devices is ~~directly~~ electrically connected to a conductive member of an upper one of said semiconductor devices.

25. (Previously Presented) A composite semiconductor device structure, comprising at least two semiconductor devices as defined in claim 22, wherein

said at least two semiconductor devices are stacked on each other, and

a conductive line pattern extending from a first electrode on a first major surface of a lower one of said semiconductor devices is connected via a bump to a conductive line pattern extending from a second electrode on a second major surface of an upper one of said semiconductor devices.

Claim 26. (Cancelled)

27. (New) The composite semiconductor device structure according to claim 24, wherein, the conductive member of a lower one of said semiconductor devices is electrically connected to a conductive member of an upper one of said semiconductor devices via a metal bump.

28. (New) The composite semiconductor device structure according to claim 24, wherein, the conductive member is directly fixed on the side surface of the semiconductor chip.